

Attorney Docket No.: 01CON211P

**In the Claims:****Claim 1 (currently amended):** An integrated circuit chip comprising:

a first interconnect metal layer;

a first intermetallic dielectric layer situated over said first interconnect metal layer;

a metal resistor situated over said first intermetallic dielectric layer, said metal

resistor being only connected to a second interconnect metal layer;

a dielectric cap layer patterned on said metal resistor;

a second intermetallic dielectric layer formed over said dielectric cap layer and  
said metal resistor;

said second interconnect metal layer over said second intermetallic dielectric layer,

wherein said first and second interconnect metal layers are adjacent to each other;a first intermediate via connected to a first terminal of said metal resistor, said first  
intermediate via being further connected to a first metal segment patterned in said second  
interconnect metal layer;a second intermediate via connected to a second terminal of said metal resistor,  
said second intermediate via being further connected to a second metal segment patterned  
in said second interconnect metal layer.**Claim 2 (original):** The integrated circuit chip of claim 1 wherein said metal  
resistor is selected from the group consisting of titanium nitride and tantalum nitride.

Attorney Docket No.: 01CON211P

**Claim 3 (original):** The integrated circuit chip of claim 1 wherein said first interconnect metal layer comprises aluminum.

**Claim 4 (original):** The integrated circuit chip of claim 1 wherein said first intermetallic dielectric layer comprises HDPCVD silicon dioxide.

**Claim 5 (original):** The integrated circuit chip of claim 1 wherein said second intermetallic dielectric layer comprises undoped silica glass.

**Claim 6 (canceled).**

**Claim 7 (previously presented):** The integrated circuit chip of claim 1 wherein said dielectric cap layer comprises silicon nitride.

**Claim 8 (original):** The integrated circuit chip of claim 1 further comprising an oxide cap layer situated between said metal resistor and said first intermetallic dielectric layer.

**Claim 9 (original):** The integrated circuit chip of claim 8 wherein said oxide cap layer comprises PECVD silicon dioxide.

Attorney Docket No.: 01CON211P

**Claim 10 (currently amended):** An integrated circuit chip comprising:

- a first interconnect metal layer;
- a first intermetallic dielectric layer situated over said first interconnect metal layer;
- a metal resistor situated over said first intermetallic dielectric layer, said metal resistor being only connected to a second interconnect metal layer;
- a dielectric cap layer patterned on said metal resistor;
- a second intermetallic dielectric layer formed over said dielectric cap layer and said metal resistor;
- said second interconnect metal layer over said second intermetallic dielectric layer,

wherein said first and second interconnect metal layers are adjacent to each other;

- a first intermediate via connected to a first terminal of said metal resistor and said second interconnect metal layer;
- a second intermediate via connected to a second terminal of said metal resistor and said second interconnect metal layer.

**Claim 11 (original):** The integrated circuit chip of claim 10 wherein said metal resistor is selected from the group consisting of titanium nitride and tantalum nitride.

**Claim 12 (original):** The integrated circuit chip of claim 10 wherein said first intermetallic dielectric layer comprises HDPCVD silicon dioxide.

Attorney Docket No.: 01CON211P

**Claim 13 (original):** The integrated circuit chip of claim 10 wherein said second intermetallic dielectric layer comprises undoped silica glass.

**Claim 14 (canceled).**

**Claim 15 (previously presented):** The integrated circuit chip of claim 10 wherein said dielectric cap layer comprises silicon nitride.

**Claim 16 (original):** The integrated circuit chip of claim 10 wherein said first interconnect metal layer comprises aluminum.

**Claim 17 (original):** The integrated circuit chip of claim 10 further comprising an oxide cap layer situated between said metal resistor and said first intermetallic dielectric layer.

**Claim 18 (original):** The integrated circuit chip of claim 17 wherein said oxide cap layer comprises PECVD silicon dioxide.

**Claims 19-27 (canceled).**

Attorney Docket No.: 01CON211P

**Claim 28 (previously presented):** The integrated circuit chip of claim 1 wherein said metal resistor is not connected from below.

**Claim 29 (previously presented):** The integrated circuit chip of claim 1 wherein the thickness of said metal resistor is approximately 100.0 Angstroms to 1500.0 Angstroms.

**Claim 30 (previously presented):** The integrated circuit chip of claim 10 wherein said metal resistor is not connected from below.

**Claim 31 (previously presented):** The integrated circuit chip of claim 10 wherein the thickness of said metal resistor is approximately 100.0 Angstroms to 1500.0 Angstroms.